

isc N-Channel MOSFET Transistor IPD135N08N3,IIPD135N08N3

FEATURES

- Static drain-source on-resistance: R_Ds(on)≤13.5mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

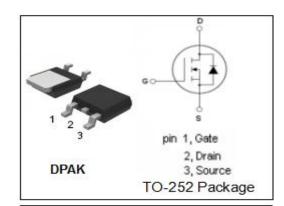
· High frequency switching

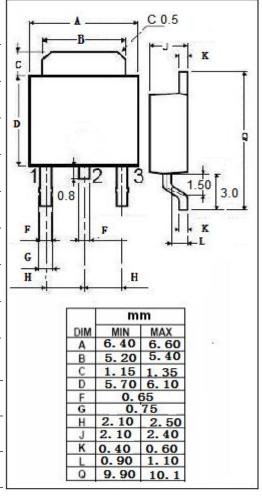
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------|------------|--|
| V _{DSS} | Drain-Source Voltage | 80 | V | |
| V _{GS} | Gate-Source Voltage | ±20 | V | |
| ID | Drain Current-Continuous | 45 | Α | |
| I _{DM} | Drain Current-Single Pulsed 18 | | А | |
| P _D | Total Dissipation @T _C =25°C | 79 | W | |
| Tj | Max. Operating Junction Temperature 175 | | $^{\circ}$ | |
| T _{stg} | Storage Temperature | -55~175 | $^{\circ}$ | |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------|---------------------------------------|-----|------|
| Rth(j-c) | Channel-to-case thermal resistance | 1.9 | °C/W |
| Rth(j-a) | Channel-to-ambient thermal resistance | 62 | °C/W |







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT | | | |
|---------------------|--------------------------------|--|-----|-----|------|------|--|--|--|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =1mA | 80 | | | V | | | |
| V _{GS(th)} | Gate Threshold Voltage | VDS=VGS; I _D =33 μ A | 2 | | 3.5 | V | | | |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D =45A | | | 13.5 | mΩ | | | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = 20V | | | 0.1 | μА | | | |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =80V; V _{GS} = 0V | | | 1 | μА | | | |
| V _{SD} | Diode forward voltage | I _F =45A, V _{GS} = 0V | | | 1.2 | V | | | |

NOTICE:

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